



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _c = +25°C
40V	10.8mΩ @ V _{GS} = 10V	30.2A
	15mΩ @ V _{GS} = 4.5V	25.6A

Features

- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed

Description and Applications

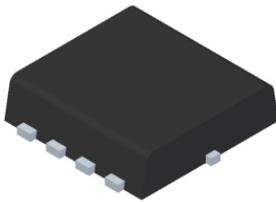
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor controls
- Power-management functions
- DC-DC converters

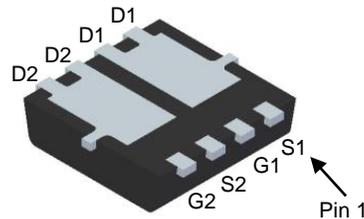
Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.023 grams (Approximate)

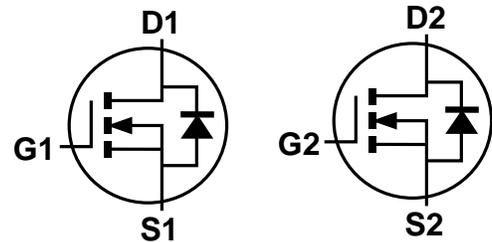
PowerDI3333-8 (Type UXC)



Top View



Bottom View



Equivalent Circuit

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 6), $V_{GS} = 10\text{V}$	I_D	$T_C = +25^\circ\text{C}$	30.2
		$T_C = +100^\circ\text{C}$	24.2
Continuous Drain Current (Note 5), $V_{GS} = 10\text{V}$	I_D	$T_A = +25^\circ\text{C}$	11.9
		$T_A = +70^\circ\text{C}$	9.5
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	120	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	16.4	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	120	A
Avalanche Current, $L = 0.1\text{mH}$ (Note 7)	I_{AS}	22.1	A
Avalanche Energy, $L = 0.1\text{mH}$ (Note 7)	E_{AS}	24.4	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	2.34
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	53.7
Total Power Dissipation (Note 6)	P_D	$T_C = +25^\circ\text{C}$	14.8
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	8.43
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 32\text{V}, V_{GS} = 0$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.2	1.4	2.3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8.4	10.8	m Ω	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	10.9	15		$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	$V_{GS} = 0, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	891	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0,$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	490	—		
Reverse Transfer Capacitance	C_{rss}	—	14.8	—		
Gate Resistance	R_g	—	1.87	—	Ω	$V_{DS} = 0, V_{GS} = 0, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	14.0	—	nC	$V_{DS} = 20\text{V}, I_D = 20\text{A}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	6.72	—		
Gate-Source Charge	Q_{gs}	—	1.04	—		
Gate-Drain Charge	Q_{gd}	—	2.52	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.95	—	ns	$V_{DD} = 20\text{V}, V_{GS} = 10\text{V},$ $R_G = 3\Omega, I_D = 20\text{A}$
Turn-On Rise Time	t_r	—	5.41	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	15.4	—		
Turn-Off Fall Time	t_f	—	8.53	—		
Body Diode Reverse-Recovery Time	t_{RR}	—	56.6	—	ns	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse-Recovery Charge	Q_{RR}	—	40.0	—	nC	

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

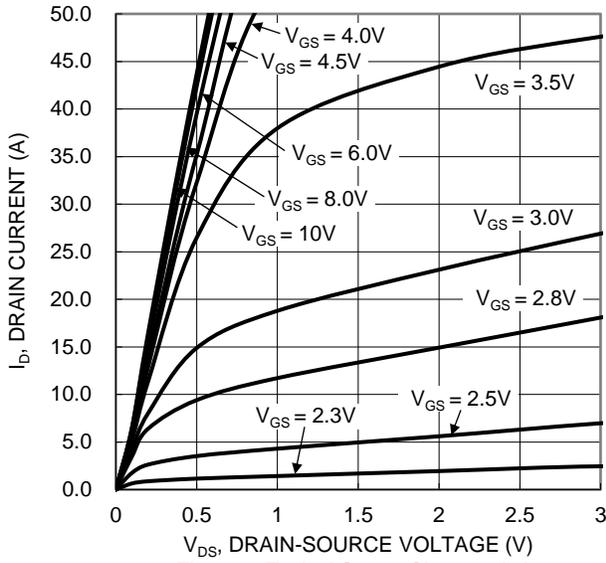


Figure 1. Typical Output Characteristic

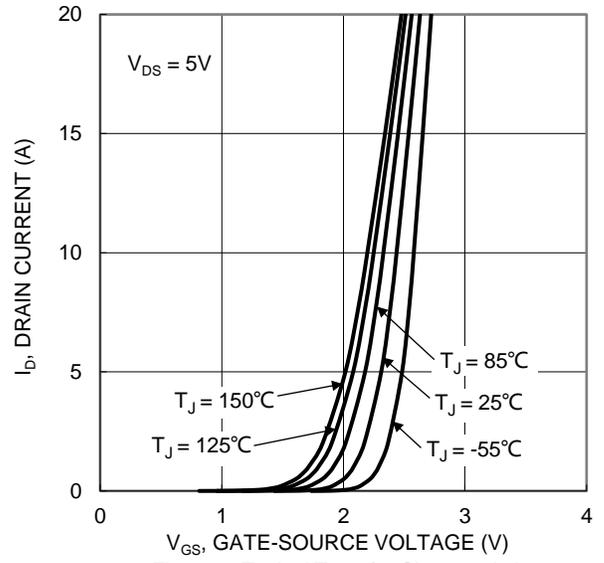


Figure 2. Typical Transfer Characteristic

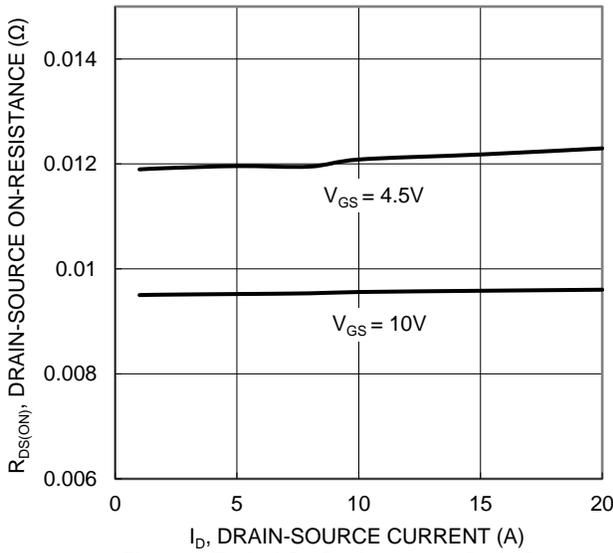


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

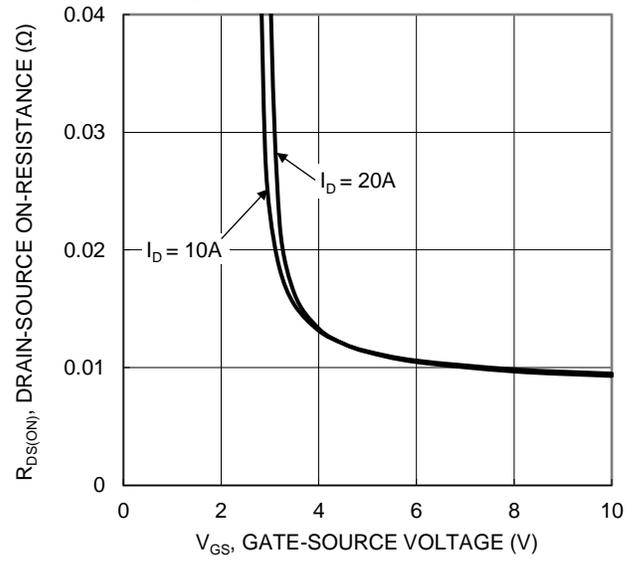


Figure 4. Typical Transfer Characteristic

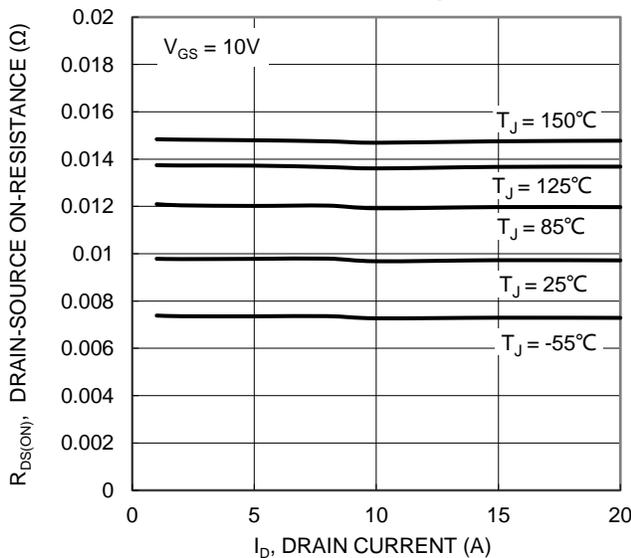


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

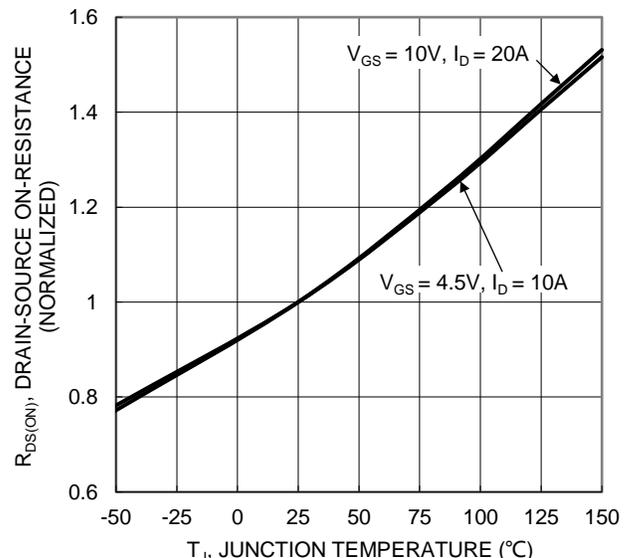


Figure 6. On-Resistance Variation with Junction Temperature

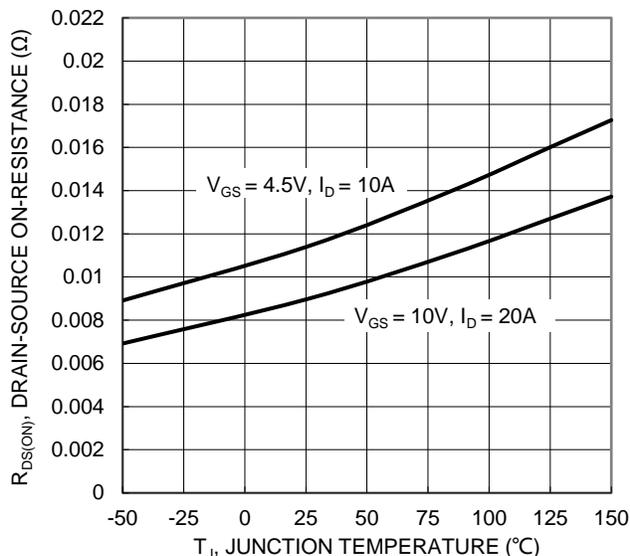


Figure 7. On-Resistance Variation with Junction Temperature

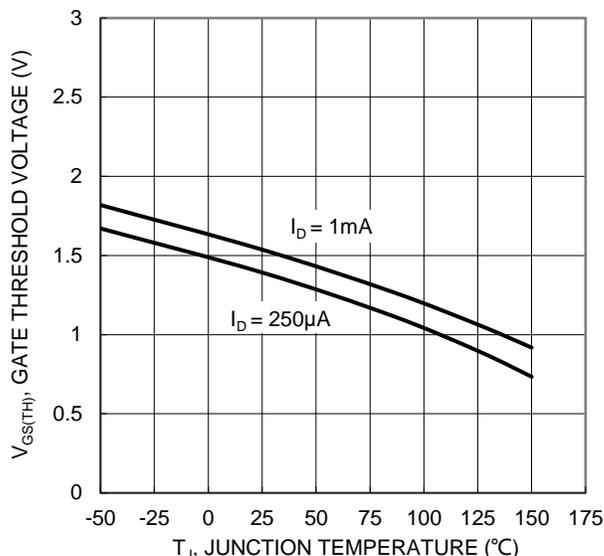


Figure 8. Gate Threshold Variation vs. Junction Temperature

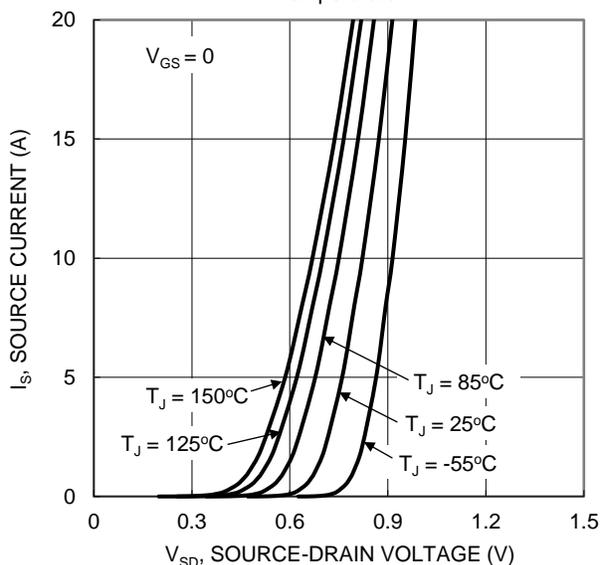


Figure 9. Diode Forward Voltage vs. Current

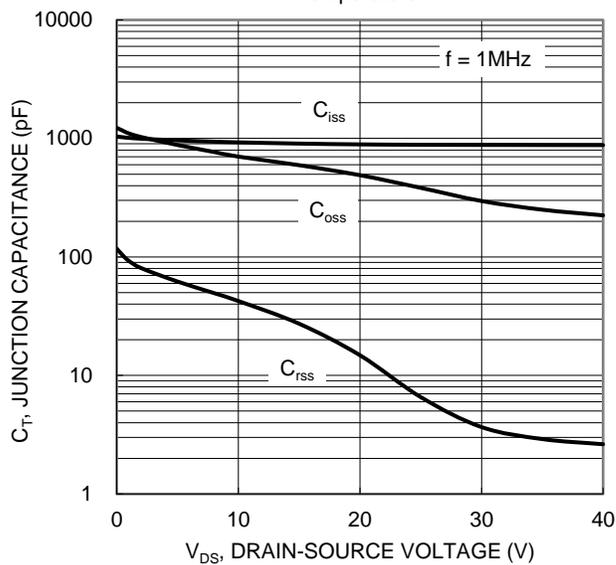


Figure 10. Typical Junction Capacitance

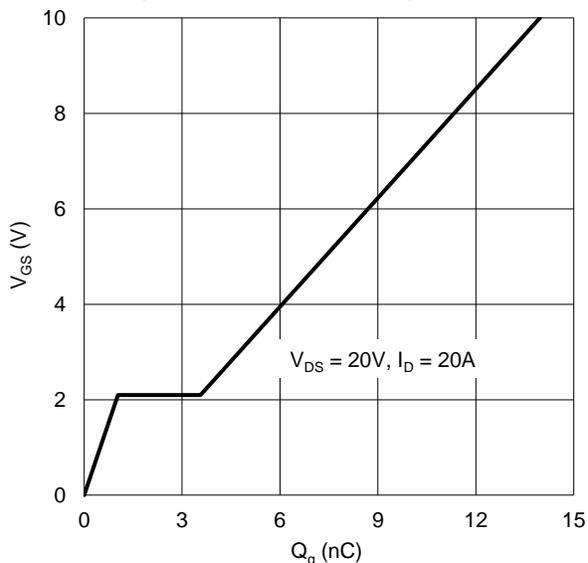


Figure 11. Gate Charge

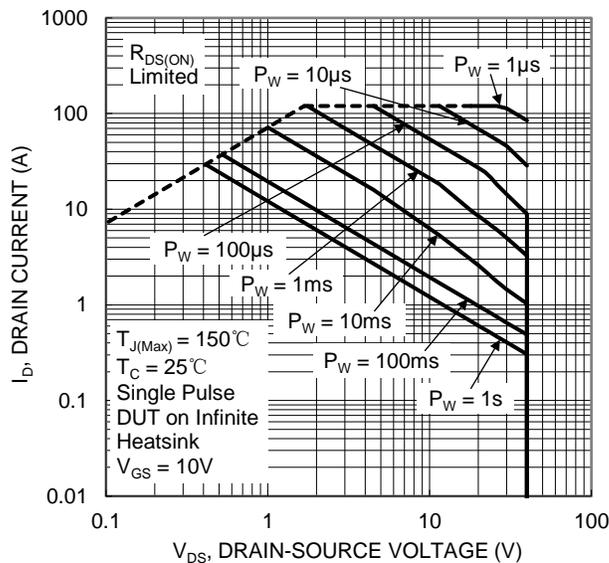


Figure 12. SOA, Safe Operation Area

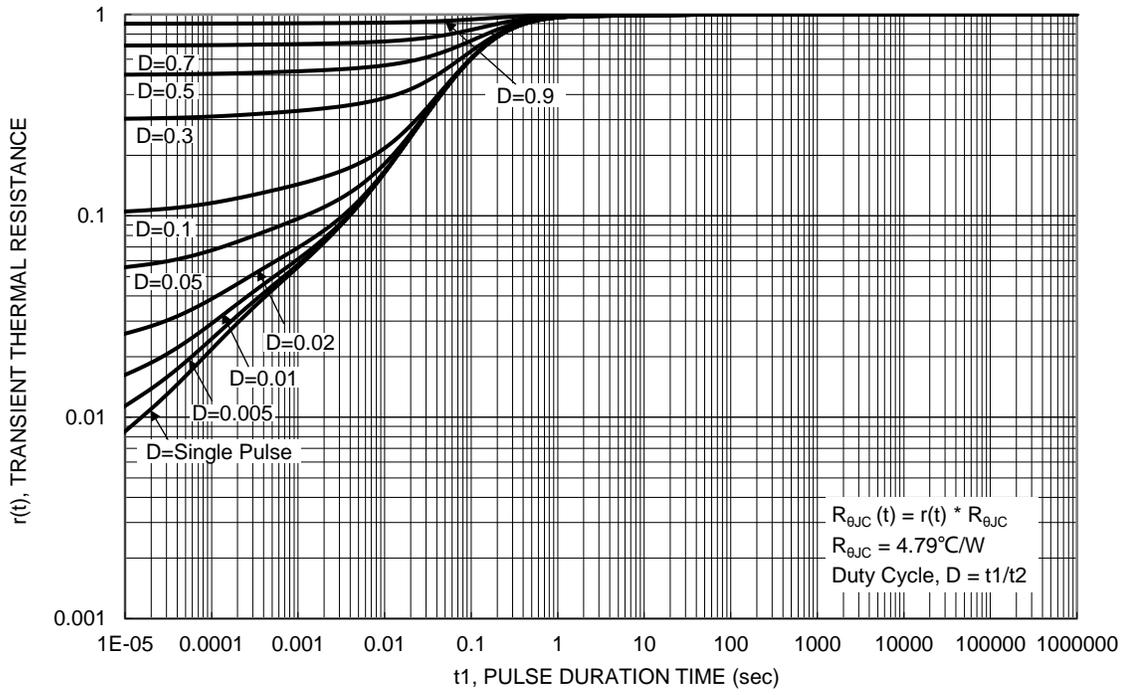
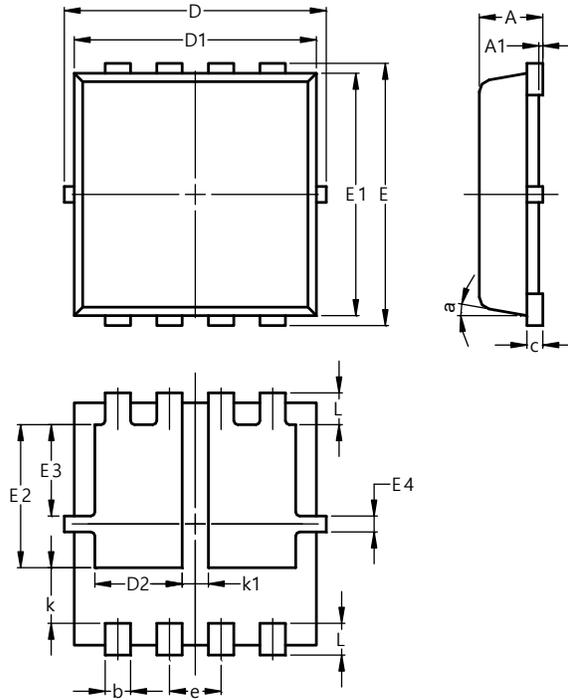


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

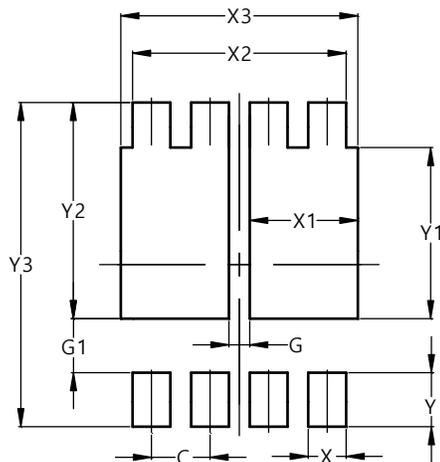
PowerDI3333-8 (Type UXC)



PowerDI3333-8 (Type UXC)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	0.90	1.30	1.10
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
L	0.30	0.50	0.40
k	0.50	0.90	0.70
k1	0.13	0.53	0.33
a	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.600
X	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600